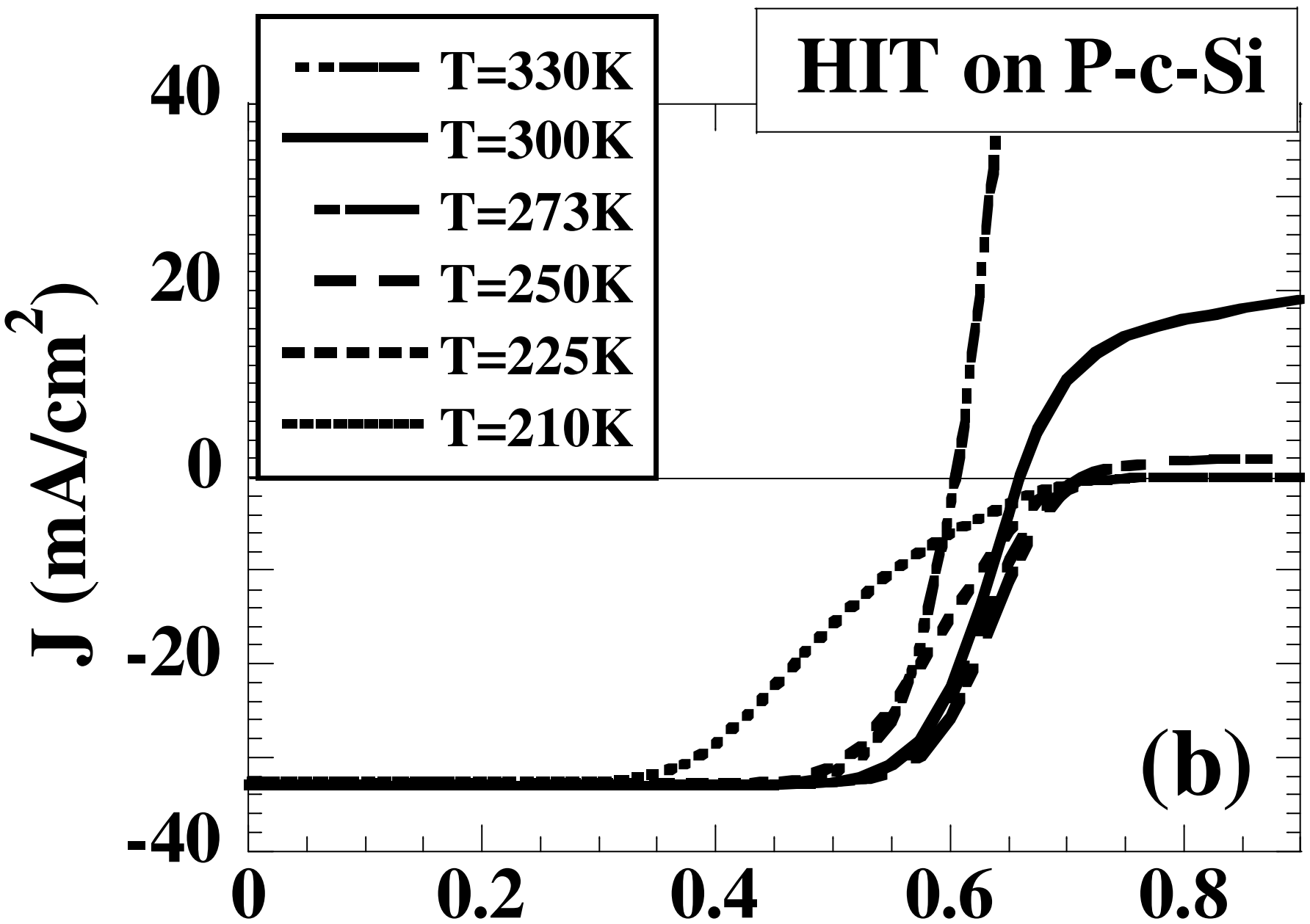
HIT on P-c-Si
T=330K
T=300K
T=273K
T=250K
T=225K
T=210K
J (mA/cm^2)
40
20
0
-20
-40
0
0.2
0.4
0.6
0.8
(b)